

under 35 U.S.C. § 120; and this application claims priority of Application No. 99/1909 filed in Korea on January 22, 1999 under 35 U.S.C. § 119.--

*In the Claims:*

Please amend the claims as follows:

1. (Twice Amended) A semiconductor device comprising:

a semiconductor substrate having a first conductivity type; and  
twin wells formed in adjacent regions of a surface portion of said semiconductor substrate,

a first of the twin wells having a second conductivity type formed in a first portion of the semiconductor substrate such that, in a direction of depth, a junction exists between the first twin well and said semiconductor substrate, and

a second of the twin wells having the first conductivity type formed in a second portion of the semiconductor substrate such that, in a direction of depth, a junction exists between the second twin well and said semiconductor substrate, wherein said substrate has no buried implanted layer beneath the twin wells, and said first and second wells have a substantially uniform junction depth at substantially all points where said junction exists.